



UPDATE CHANGE NOTIFICATION # 16790DCGeneric Copy

Issue Date: 13-Nov-2013

TITLE: Update Change Notification to FPCN16790DC to correct the description from "Wafer Fab Transfer from Gifu to UMCT" to "Wafer Fab Transfer from UMCJ to UMCT" for EFC4612R-TR product.

PROPOSED FIRST SHIP DATE: 13-Feb-2014 (or earlier with customer approval)
<The actual ship date will be different by each product, please check the responsible Sales Person.>

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

SAMPLES: Contact your local ON Semiconductor Sales Office

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:
Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com

ADDITIONAL RELIABILITY DATA: Available
Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:
Update Change Notification to FPCN

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

FPCN16790DC announced the transfer of product (EFC4612R-TR) from SANYO wafer fabrication site located in Gifu to the United Microelectronics Corporation Taiwan (UMCT) on 19-Sep-2013.

This is an update notification to correct former announce of FPCN16790DC for EFC4612R-TR. The description of origin transfer site is corrected from "SANYO wafer fabrication in Gifu" to "United Microelectronics Corporation in Japan" as following:

FPCN16790DC: From SANYO wafer fabrication in Gifu to UMC in Taiwan (UMCT)
UN16790DC : From UMC in Japan (UMCJ) to UMC in Taiwan (UMCT)

UMCT manufacturing process and procedures will be the same as UMCJ. There will be no changes in device functionality, specification and electrical characteristics. Reliability will continue to meet or exceed ON Semiconductor's highest standards.

We apologize that FPCN16790DC has insufficient description.

**UPDATE CHANGE NOTIFICATION #16790DC****RELIABILITY DATA SUMMARY:**

Test:	Conditions:	Interval:	Results
High Temperature Reverse Bias	Ta=150degC, VGDO=20V	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03×10^5 Pa, 100%	50 hrs	Pass
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Resistance to Soldering heat (Reflow)	Solder Temp.: 260degC \pm 5degC	10s	Pass
Solderability	Solder Temp.: 245degC \pm 5degC	5s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY:

There is no change in electrical parametric performance. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected parts:

EFC4612R-TR